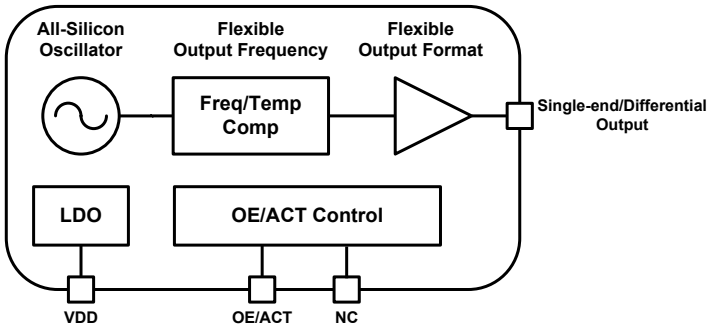
AS5001 Low Jitter Differential Silicon Oscillator

Description

The AS5001 Arcadium™ all-silicon oscillator utilizes proprietary frequency synthesis and sensor technologies to provide a quartz-free, MEMS-free, low jitter clock at any output frequency. The device is factory-programmed to output frequencies ranging from 10 kHz to 350 MHz with 0.026 ppb resolution and maintains low jitter across its operating range. The AS5001 uses on-chip temperature and strain sensors, and an advanced LC tank architecture to achieve excellent reliabilities even in high impact shock scenarios.

AS5001's on-chip power supply filtering provides industry-leading power supply noise rejection, simplifying the task of generating low jitter clocks in noisy systems that use switched- mode power supplies. Offered in a variety of industry-standard packages, the AS5001 has a dramatically simplified supply chain that enables Aeonsemi to ship samples shortly after receipt of order. The AS5001 is factoryconfigurable for a wide variety of user specifications, including frequency, output format, and OE pin assignment. Specific configurations are factory programmed at time of shipment, eliminating the long lead times associated with custom oscillators. This process also guarantees 100% electrical testing of every device before shipment.



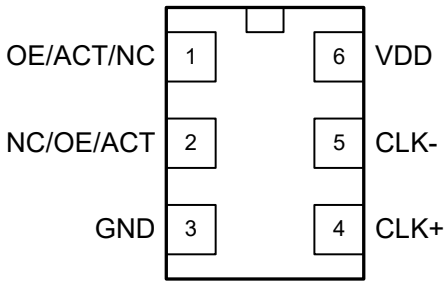
Key Features

- Quartz-free and MEMS-free without mechanical moving parts
- LVCMOS output: 10 kHz to 212.5 MHz
- Differential output: 10 kHz to 350 MHz
- Low jitter: 350 fs Typ
  (12 kHz – 20 MHz, @156.25 MHz)
- Compliant to PCIe Gen 1/2/3/4/5/6 jitter spec
- Temperature stability:
  - ±20 ppm (-20 to 85 ℃)
  - ±35 ppm (-40 to 85 ℃)
  - ±35 ppm (-40 to 105 ℃)
- Integrated LDO for on-chip power supply noise filtering
- Support 1.8V, 2.5V, 3.3V V_{DD} supply operation
- Industrial standard 3225 and 5032 package footprints

Application

- 1G/10G/40G/100G/200G Ethernet
- Servers, switches, storage, NICs, search acceleration
- Test and measurement
- Clock and data recovery
- FPGA/ASIC clocking

Pin definition



Top view

Pin#	Description
1,2	OE = Output enable. Active high ACT = Device active. Active high NC = Not connect
3	GND = Ground
4	CLK+ = Clock output
5	CLK- = Complementary clock output
6	VDD = Power supply

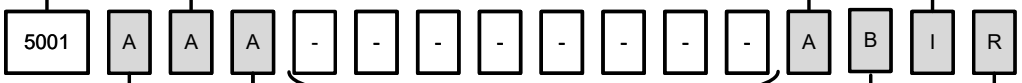
1. Ordering Guide

XO Series	Description
5001	Fixed Frequency

	Device Type
A	General
X[1]	Factory defined setting

	Package
A	5032
B	3225

	Temperature Grade
I	-40 to 85 °C
E	-40 to 105 °C



Signal Format	VDD Range	Code
LVPECL (Standard)	2.5, 3.3 V	A
LVPECL (Self-Biased)	2.5, 3.3 V	B
LVDS	1.8 V	C
LVDS	2.5, 3.3 V	D
CML	1.8, 2.5, 3.3 V	E
HCSL (50ohm Termination)	1.8, 2.5, 3.3 V	F
HCSL (42.5ohm Termination)	1.8, 2.5, 3.3 V	G
Single CMOS (Pin4)	1.8, 2.5, 3.3 V	H
Dual CMOS (In-Phase)	1.8, 2.5, 3.3 V	I
Dual CMOS (Complementary)	1.8, 2.5, 3.3 V	J

	Description	Pin #
A	OE	1
B	OE	2
C	ACT	1
D	ACT	2

Device Revision

Code	Packing type	Qty
T	7-inch reel	250
R	13-inch reel	2500
<blank>	Bulk	Sample

Frequency Code[2]	Description
Mxxxxxxx	FCLK < 1 MHz
xMxxxxxx	1 MHz <= FCLK < 10 MHz
xxMxxxxx	10 MHz <= FCLK < 100 MHz
xxxMxxxx	100 MHz <= FCLK <= 350 MHz

Note:

1. “X” refers to the ID for the unique configuration with factory-defined settings, the value ranges from “B” to “Z”.
2. For example: 125 MHz = 125M0000; 33.33333 MHz = 33M33333.

2. Electrical Specifications

Table 2.1. Electrical Specifications

Parameter	Symbol	Min	Typ	Max	Unit	Note
Operating Temperature Range						
Temperature Range	T_A	-40	—	85	℃	Industrial grade
		-40	—	105	℃	Extended industrial grade
Supply Voltage and Power Consumption						
Supply Voltage	V_{DD}	1.71	—	3.47	V	
Supply Current (F_{CLK} = 156.25 MHz)	I_{DD}	—	40	50	mA	Tristate Hi-Z (OE = 0)
		—	1	2	mA	Ready State (ACT = 0)
		—	70	80	mA	LVPECL (Standard)
		—	60	70	mA	LVPECL (Self-Biased)
		—	45	55	mA	LVDS
		—	60	70	mA	HCSL
		—	60	70	mA	CML
		—	40	55	mA	Single LVCMOS (C_L = 15 pF)
		—	60	70	mA	Dual LVCMOS (C_L = 15 pF)
Frequency Range						
Frequency Range	F_{CLK}	0.01	—	212.5	MHz	LVCMOS output
		0.01	—	350	MHz	Differential output
Frequency Tolerance						
Initial frequency accuracy	F_{INIT}	-10	—	10	ppm	Inclusive of initial frequency tolerance at 25℃ and variations over supply voltage, load and humidity after soldering-reflow shift settles.
Temperature stability	F_{STAB}	-20	—	20	ppm	-20 - 85℃
		-35	—	35	ppm	-40 - 85℃
		-35	—	35	ppm	-40 - 105℃
Aging	F_{AGING}	-5	—	5	ppm	10 Year at 25 ℃
IO Characteristics						
Output enable (OE)	V_{IH}	0.7×V_{DD}	—	—	V	Input high voltage
	V_{IL}	—	—	0.3×V_{DD}	V	Input low voltage
	R_{PUP}	—	50	—	kΩ	Internal pull-up resistor to V_{DD}
	T_D	—	—	3	us	Output disable time, F_{CLK} >10 MHz
	T_E	—	—	20	us	Output enable time, F_{CLK} >10 MHz
Device active (ACT)	V_{IH}	0.7×V_{DD}	—	—	V	Input high voltage
	V_{IL}	—	—	0.3×V_{DD}	V	Input low voltage
	R_{PUP}	—	50	—	kΩ	Internal pull-up resistor to V_{DD}
	T_D	—	—	3	us	Output disable time, F_{CLK} >10 MHz
	T_S	—	—	40	us	Device standby time, F_{CLK} >10 MHz
	T_E	—	—	400	us	Device enable time, F_{CLK} >10 MHz

Continued on next page

Parameter	Symbol	Min	Typ	Max	Unit	Note
Output Characteristics						
Powerup time	T_{OSC}	—	—	4	ms	Time from power reaches 0.9 × V_{DD} to output frequency (F_{CLK}) within spec
Duty cycle	DC	45	—	55	%	All formats
Rise/Fall time (20% to 80% VPP)	$T_{R/F}$	—	0.5	1.5	ns	LVCMOS (C_L = 15 pF)
		—	—	350	ps	LVPECL / LVDS / CML
		—	—	550	ps	HCSL
LVPECL (Standard)	V_{OC}	V_{DD}-1.55	V_{DD}-1.4	V_{DD}-1.25	V	Mid-level
	V_O	1.35	1.6	1.85	V_{PP}	Swing (Diff)
LVPECL (Self-Biased)	V_O	1.35	1.6	1.85	V_{PP}	Swing (Diff)
LVDS	V_{OC}	1.125	1.20	1.275	V	Mid-level (2.5V, 3.3V V_{DD})
		0.78	0.85	0.92	V	Mid-level (1.8V V_{DD})
	V_O	0.64	0.8	0.96	V_{PP}	Swing (Diff)
HCSL (R_{TERM} = 50 Ω)	V_{OC}	0.35	0.4	0.45	V	Mid-level
	V_O	1.28	1.6	1.92	V_{PP}	Swing (Diff)
HCSL (R_{TERM} = 42.5 Ω)	V_{OC}	0.35	0.4	0.45	V	Mid-level
	V_O	1.29	1.62	1.94	V_{PP}	Swing (Diff)
CML	V_{OC}	V_{DD}-0.35	V_{DD}-0.4	V_{DD}-0.45	V	Mid-level
	V_O	1.28	1.6	1.92	V_{PP}	Swing (Diff)
LVCMOS	V_{OH}	0.83×V_{DD}	—	—	V	C_L = 15 pF
	V_{OL}	—	—	0.17×V_{DD}	V	
Phase Noise and Jitter						
RMS jitter BW: 12k - 20MHz	R_J	—	350	750	fs	F_{CLK} >= 100 MHz
		—	450	750	fs	F_{CLK} >= 25 MHz
Phase noise 156.25MHz LVDS output V_{DD} = 1.8 - 3.3V	PN_{1k}	—	-80	—	dBc/Hz	Phase noise at 1kHz offset
	PN_{10k}	—	-110	—	dBc/Hz	Phase noise at 10kHz offset
	PN_{100k}	—	-133	—	dBc/Hz	Phase noise at 100kHz offset
	PN_{1M}	—	-152	—	dBc/Hz	Phase noise at 1MHz offset
	PN_{10M}	—	-161	—	dBc/Hz	Phase noise at 10MHz offset
PSRR						
Spurs from power noise 50mV ripple V_{DD} = 1.8V	PSRR	—	-76	—	dBc	100 kHz sine wave
		—	-75	—	dBc	200 kHz sine wave
		—	-75	—	dBc	500 kHz sine wave
		—	-75	—	dBc	1 MHz sine wave
Spurs from power noise 50mV ripple V_{DD} = 2.5 or 3.3V	PSRR	—	-83	—	dBc	100 kHz sine wave
		—	-83	—	dBc	200 kHz sine wave
		—	-83	—	dBc	500 kHz sine wave
		—	-82	—	dBc	1 MHz sine wave
Thermal Resistance						
Thermal resistance 5032 6-pin DFN Still air	θ_{JA}	—	105	—	℃/W	Junction to ambient
	θ_{JB}	—	81	—	℃/W	Junction to board
	T_J	—	125	—	℃/W	Maximum junction temperature
Thermal resistance 3225 6-pin DFN Still air	θ_{JA}	—	108	—	℃/W	Junction to ambient
	θ_{JB}	—	84	—	℃/W	Junction to board
	T_J	—	125	—	℃/W	Maximum junction temperature

Table 2.2. PCIe Clock Output Performance (100MHz HCSL)

Parameter	Specification	Max	Unit	Test Condition
PCIe Gen 1.1	N/A	0.311	ps	Includes PLL BW 1.5 - 22 MHz Peaking = 3dB, T_D=10 ns
PCIe Gen 2.1	3.1	0.022	ps	Includes PLL BW 5MHz & 8 - 16 MHz Peaking = 0.01 - 1 dB & 3 dB, T_D=12ns Low Band, F $<$ 1.5 MHz
	3.0	0.259	ps	Includes PLL BW 5MHz & 8 - 16 MHz Peaking = 0.01 - 1 dB & 3 dB, T_D=12ns High Band, 1.5 MHz $<$ F $<$ Nyquist
PCIe Gen 3.0 common clock	1	0.085	ps	Includes PLL BW 2 - 4 MHz & 5 MHz Peaking = 0.01 - 2dB & 1dB, T_D=12 ns CDR = 10 MHz
PCIe Gen 4.0 common clock	0.5	0.085	ps	Includes PLL BW 2 - 4 MHz & 5 MHz Peaking = 0.01 - 2dB & 1dB, T_D=12 ns CDR = 10 MHz
PCIe Gen 5.0 common clock	0.15	0.033	ps	Includes PLL BW 500 kHz - 1.8 MHz Peaking = 0.01 – 2dB, T_D=12 ns CDR = 20 MHz
PCIe Gen 6.0 common clock	0.1	0.021	ps	Includes PLL BW 500 kHz – 1 MHz Peaking = 0.01 – 2dB, T_D=12 ns CDR = 10 MHz

Class	Data Rate	Architecture	Specs	Max HF RMS	Max LF RMS	Max Pk-Pk	Compliance Summary
GEN1	2.5 Gb/s	Common Clock	1.1 2.1 3.1	310.77 fs	41.59 fs	N/A	N/A
GEN2	5 Gb/s	Common Clock	1.1 2.1 3.1	259.42 fs	21.89 fs	N/A	All PASS
GEN3	8 Gb/s	Common Clock	3.1 4.0	84.54 fs	4.68 fs	N/A	All PASS
GEN4	16 Gb/s	Common Clock	4.0	84.54 fs	4.68 fs	N/A	All PASS
GEN5	32 Gb/s	Common Clock	5.0	32.92 fs	2.09 fs	N/A	All PASS
GEN6	64 Gb/s	Common Clock	6.0	21.00 fs	0.88 fs	N/A	All PASS

Figure 2.1. PCI-Express clock Compliance Summary

Table 2.3. Environmental Compliance and Package Information

Parameter	Value
Moisture sensitivity level (MSL)	1

Notes:

For additional product information not listed in the data sheet (e.g. RoHS Certifications, MSDS data, qualification data, REACH Declarations, ECCN codes, etc.), contact aeonsemi.com/contact_us

Table 2.4. Absolute Maximum Ratings[1]

Parameter	Symbol	Rating	Unit
Maximum operating temperature	T_{AMAX}	125	℃
Storage temperature	T_S	-55 - 125	℃
Supply voltage	V_{DD_MAX}	-0.5 - 3.8	V
Input voltage	V_{IN_MAX}	-0.5 - V_{DD}+0.3	V
ESD HBM (JESD22-A114)	HBM	4.0	kV
ESD CDM (JESD22-C101)	CDM	1.0	kV
Solder Temperature[2]	T_{PEAK}	260	℃
Solder time at T_{PEAK}[2]	T_P	20 - 40	sec

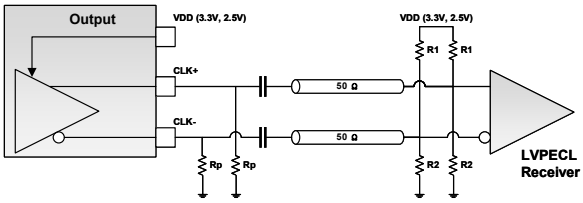
Notes:

1. Stresses beyond those listed in this table may cause permanent damage to the device. Functional operation specification compliance is not implied at these conditions. Exposure to maximum rating conditions for extended periods may affect device reliability.
2. The device is compliant with JEDEC J-STD-020.

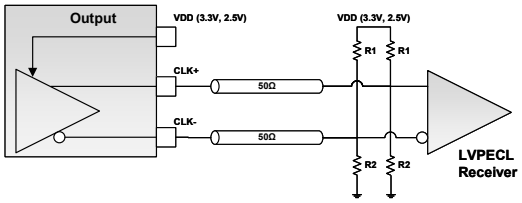
3. Recommended Output Terminations

3.1. Differential Output

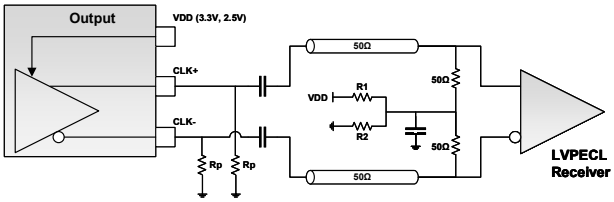
The output drivers support AC-coupled or DC-coupled terminations as shown in figures below.



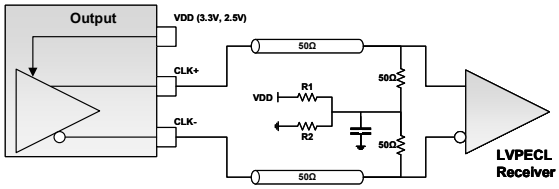
AC-Coupled LVPECL - Thevenin Termination



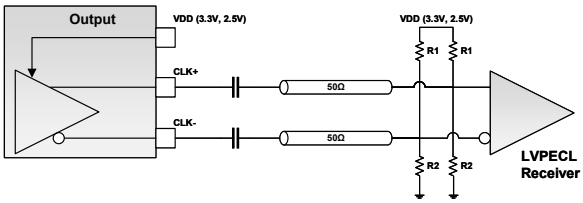
DC-Coupled LVPECL - Thevenin Termination



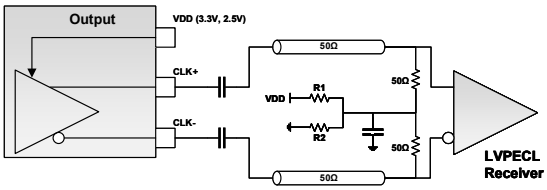
AC-Coupled LVPECL - 50 Ω with VTT Bias



DC-Coupled LVPECL - 50 Ω with VTT Bias



AC-Coupled Self-Biased LVEPCL - Thevenin Termination



AC-Coupled Self-Biased LVEPCL - 50 Ω with VTT Bias

Figure 3.1. LVPECL Output Terminations

Table 3.1. LVPECL Termination Resistor Values

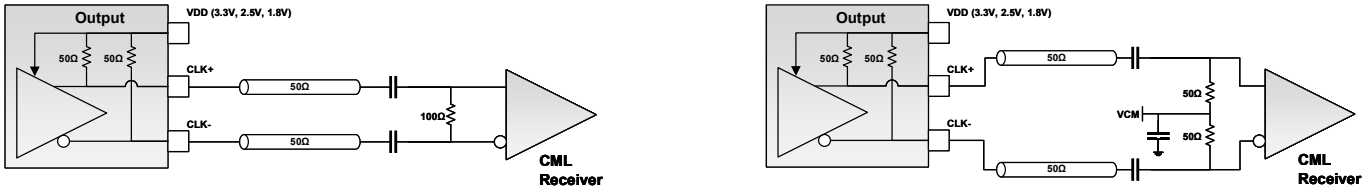
AC Coupled LVPECL Termination Resistor Values			
V_{DD}(V)	R_P	R_1	R_2
3.3 V	158 Ω	127 Ω	82.5 Ω
2.5 V	92 Ω	250 Ω	62.5 Ω

DC Coupled LVPECL Termination Resistor Values		
V_{DD}(V)	R_1	R_2
3.3 V	127 Ω	82.5 Ω
2.5 V	250 Ω	62.5 Ω

AC-Coupled LVDS

DC-Coupled LVDS

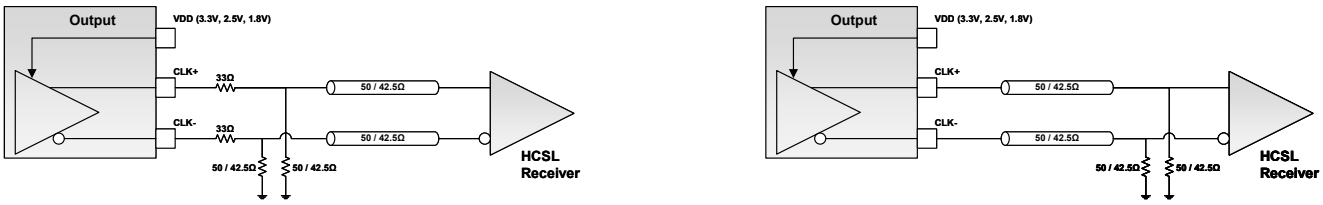
Figure 3.2. LVDS Output Terminations



AC-Coupled CML without VCM

AC-Coupled CML with VCM

Figure 3.3. CML Output Terminations



Source Terminated HCSL

Destination Terminated HCSL

Figure 3.4. HCSL Output Terminations

3.2. CMOS Output

Dual CMOS output format options support either complementary or in-phase signals for two identical frequency outputs. This feature enables replacement of multiple XOs with a single AS5001 device.

Figure 3.5. Integrated 1:2 CMOS Buffer Supports In-Phase or Complementary Outputs

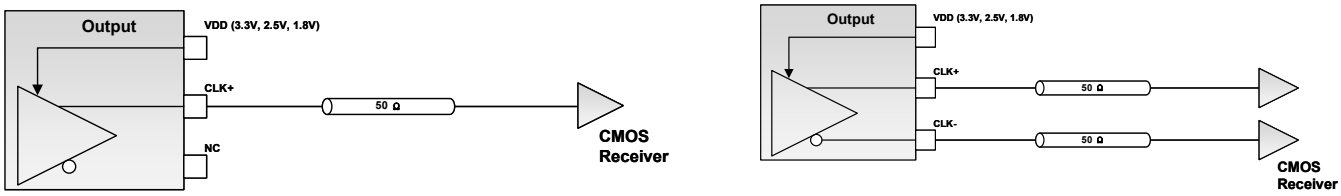


Figure 3.6. LVCMOS Output Terminations

4. Package Outline Drawing

Figure 4.1. shows the package outline drawing for the AS5001 devices. Details of dimension for different size options are listed in Table 4.1.

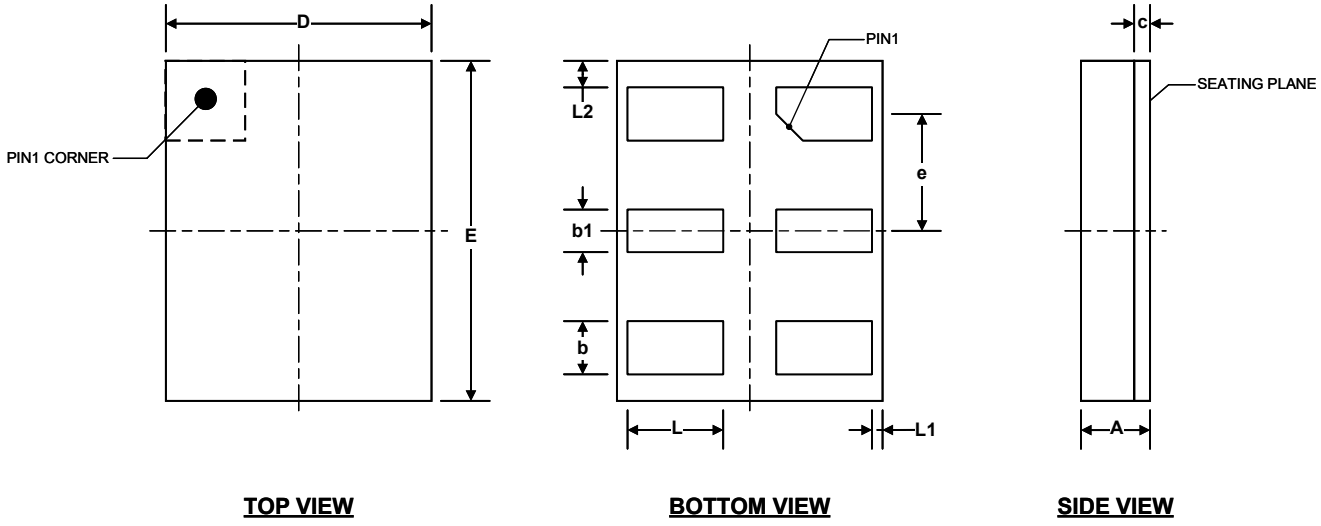


Figure 4.1. Package Outline Drawing

Table 4.1. Dimensions of Package Outline Drawing (mm)

Symbol	5032 Package	3225 Package
A	0.85 ± 0.05	0.85 ± 0.05
b	0.64 ± 0.05	0.65 ± 0.05
b1	0.64 ± 0.05	0.50 ± 0.05
D	3.20 ± 0.10	2.50 ± 0.10
e	1.27 BSC	1.175 BSC
E	4.00 ± 0.10	3.20 ± 0.10
L	0.75 ± 0.05	0.70 ± 0.05
L1	0.10 ± 0.05	0.10 ± 0.05

5. Recommended PCB Land Pattern

Figure 5.1. shows the drawing of recommended PCB land pattern for the AS5001 devices. Details of dimension for different size options are listed in Table 5.1.

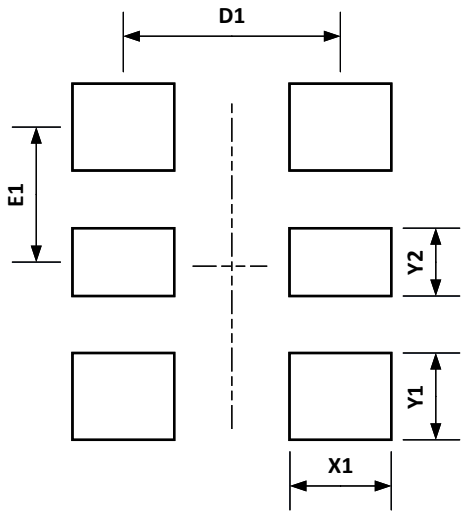


Figure 5.1. Recommended PCB Land Pattern

Table 5.1. Dimensions of Recommended PCB Land Pattern (mm)

Symbol	5032 Package	3225 Package
D1	2.35	1.70
E1	1.27	1.175
X1	1.05	1.00
Y1	0.84	0.85
Y2	0.84	0.7

Notes:

The following notes and stencil design are shared as recommendations only. A customer or user may find it necessary to use different parameters and fine-tune their SMT process as required for their application and tooling.

General

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.
3. This Land Pattern Design is based on the IPC-7351 guidelines.
4. All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05 mm.

Solder Mask Design

1. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.

Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 0.8 1 for the pads.

Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6. Top Mark

Figure 6.1. shows the top mark specifications for the AS5001 devices. Description of each line is listed in Table 6.1.

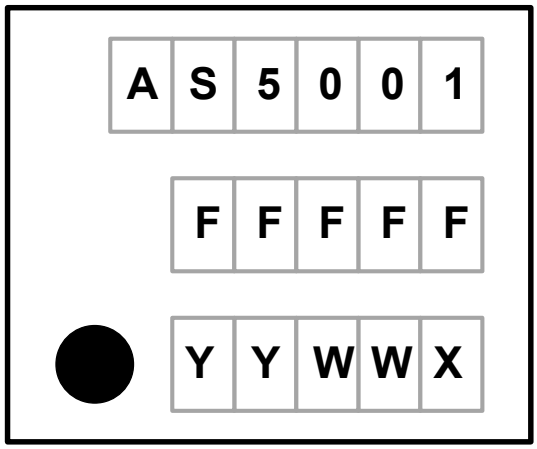


Figure 6.1. Top Mark

Table 6.1. Top Mark Description

Line	Position	Description
1	1-6	Device Name
2	1-5	Unique 5-digit Device Configuration Number
3	1	Pin 1 orientation mark (dot)
	2-3	Year (last two digits of the year), to be assigned by assembly site (ex: 2025 = 25)
	4-5	Calendar Work Week number (1-53), to be assigned by assembly site
	6	Manufacturer code

7. Packing Specification

Figure 7.1. shows the packing specifications for the AS5001 devices. Details of the tape specifications are listed in Table 7.1.

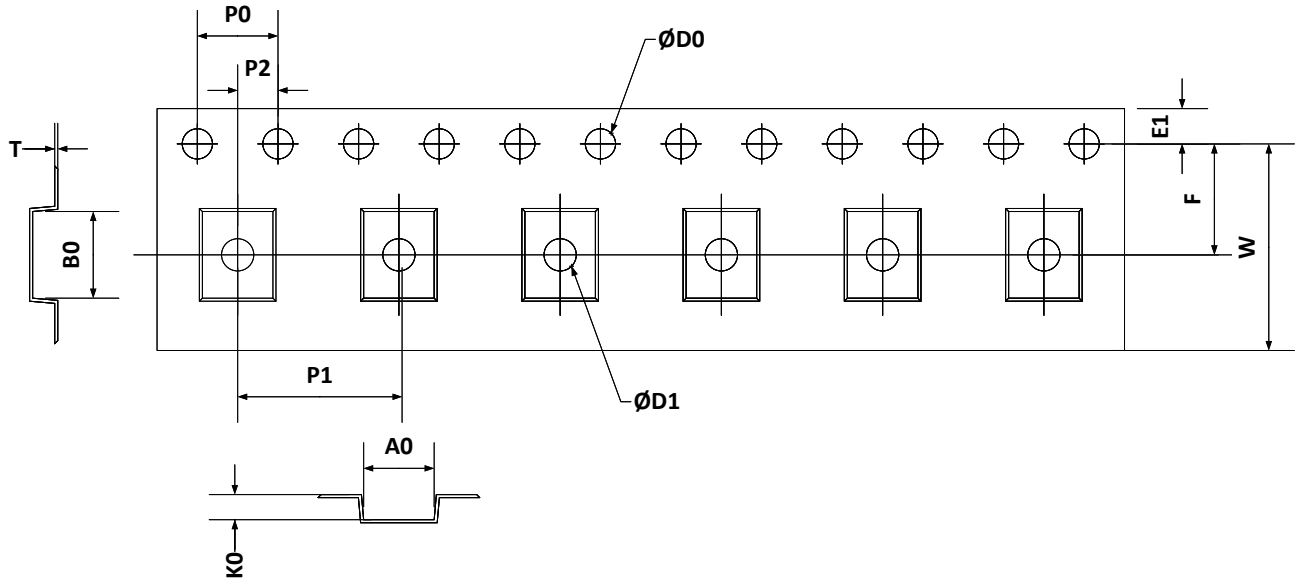


Figure 7.1. Tape Specification

Table 7.1. Dimensions of Tape (mm)

Symbol	5032 Package	3225 Package
A0	3.50 ± 0.10	2.80 ± 0.10
B0	4.30 ± 0.10	3.50 ± 0.10
K0	1.25 ± 0.10	1.05 ± 0.10
E1	1.75 ± 0.10	1.75 ± 0.10
F	5.50 ± 0.05	5.50 ± 0.05
W	12.00 ± 0.30	12.00 ± 0.30
T	0.30 ± 0.05	0.30 ± 0.05
P0	4.00 ± 0.10	4.00 ± 0.10
P1	8.00 ± 0.10	8.00 ± 0.10
P2	2.00 ± 0.05	2.00 ± 0.05
ØD0	1.50 ± 0.10	1.50 ± 0.10
ØD1	1.60 ± 0.10	1.60 ± 0.10

8. Important Notice and Disclaimer

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9. Revision History

Revision	Date	Description
1.14	Jul 2026	Correct the LVPECL resistor value and the recommended PCB land pattern value
1.13	Aug 2025	Corrected the tape specification
1.12	Aug 2024	Add packing specification
1.11	Mar 2024	Updated the frequency offset
1.10	Jul 2022	Updated the top mark specification
1.01	Dec 2021	Adjusted the PCB land pattern dimensions
1.00	Sep 2021	With certain specification update
0.95	Jun 2021	Corrected the Ordering Guide Insert -40 - 105 ℃ temperature range option Insert section ”IMPORTANT NOTICE AND DISCLAIMER”
0.20	Mar 2021	Changed the frequency range and ordering guide
0.10	Feb 2021	Initial release